

Pending

Active

- L1: (0) 10/615929
- L2: (6) (photodiode with antireflection near3 film) with ((oxide))
- L3: (1) 2 and side adj wall
- L4: (2330) (438/48,72,197,309,636) CCLS
- L5: (3849) (257/69,186,199,204,233,288,292,437,462) CCLS
- L6: (2) 4 and (photodiode with antireflection near3 film)
- L7: (12) 5 and (photodiode with antireflection near3 film)

Failed

- (0) (CMOS MOS (metal adj oxide near3 semiconductor))

Saved

- (1225) photodiode.clm. and transistor.clm.
- (637) (photodiode.clm. and transistor.clm.) and (MOS CMOS)
- (200) ((photodiode.clm. and transistor.clm.) and (MOS CMOS))
- (54) (((photodiode.clm. and transistor.clm.) and (MOS CMOS)))
- (447874) (CMOS MOS (metal adj oxide near3 semiconductor))

Search	Patent	Database	Help
Dos	USPAT US-PGPUB EPO PCT DERVENT SM TDG P Demos		
Detail Operator:	DP		P: Highlight all the terms (initially)
[ L and (photodiode with antireflection near3 film)]			

Order	Document ID	Issue Date	Pages	Title	Current	Cntr Re	Inventor	S	C	P	M	O
1	r r US 20040075153 A1	20040422	13	Semiconductor device an	257/437		Fujisawa, Tomotak	P	R	C	R	R
2	r r US 20030067011 A1	20030410	44	Zn1-xMgxSySe1-y pin-p	257/186		Ando, Koshi et al	P	R	C	R	R
3	r r US 20020030206 A1	20020314	24	Photodetector with built-	257/292		Takimoto, Takahiro	P	R	C	R	R
4	r r US 20020027239 A1	20020307	15	CMOS image sensor and	257/292	257/	Ohkubo, Hiroaki	P	R	C	R	R
5	r r US 6724018 B2	20040420	42	Zn1-xMgxSySe1-y pin-p	257/186	257/	Ando, Koshi et al	P	R	C	R	R
6	r r US 6707081 B2	20040316	23	Photodetector with built-	257/292	257/	Takimoto, Takahiro	P	R	C	R	R
7	r r US 6646317 B2	20031111	11	High power photodiode	257/436	257/	Takeuchi, Takeshi	P	R	C	C	C
8	r r US 6635912 B2	20031021	14	CMOS image sensor and	257/292	257/	Ohkubo, Hiroaki	P	R	C	R	R
9	r r US 6114740 A	20000905	27	Circuit integrating light	257/461	257/	Takimoto, Takahiro	P	R	C	R	R